

FIG. 1A

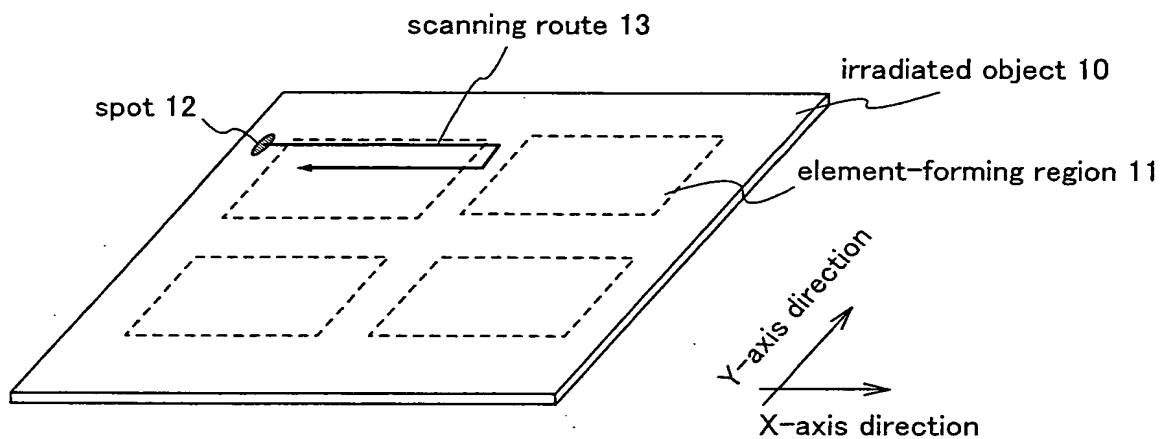


FIG. 1B

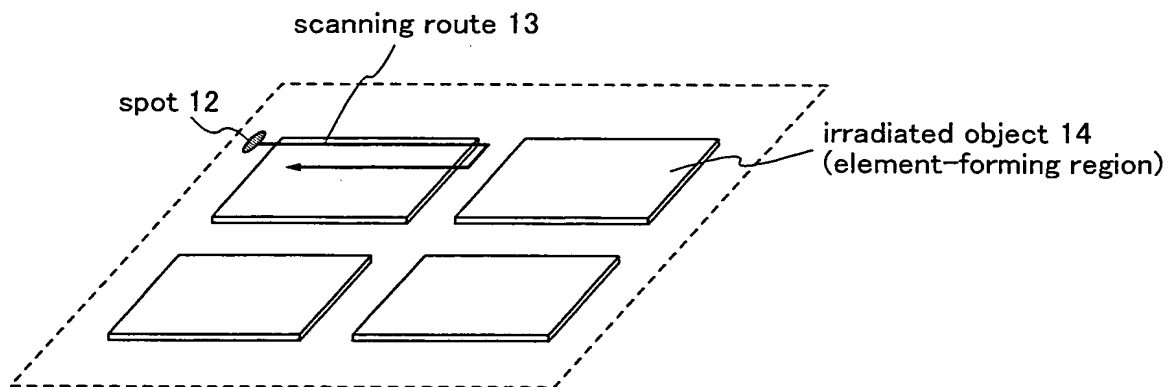


FIG. 2

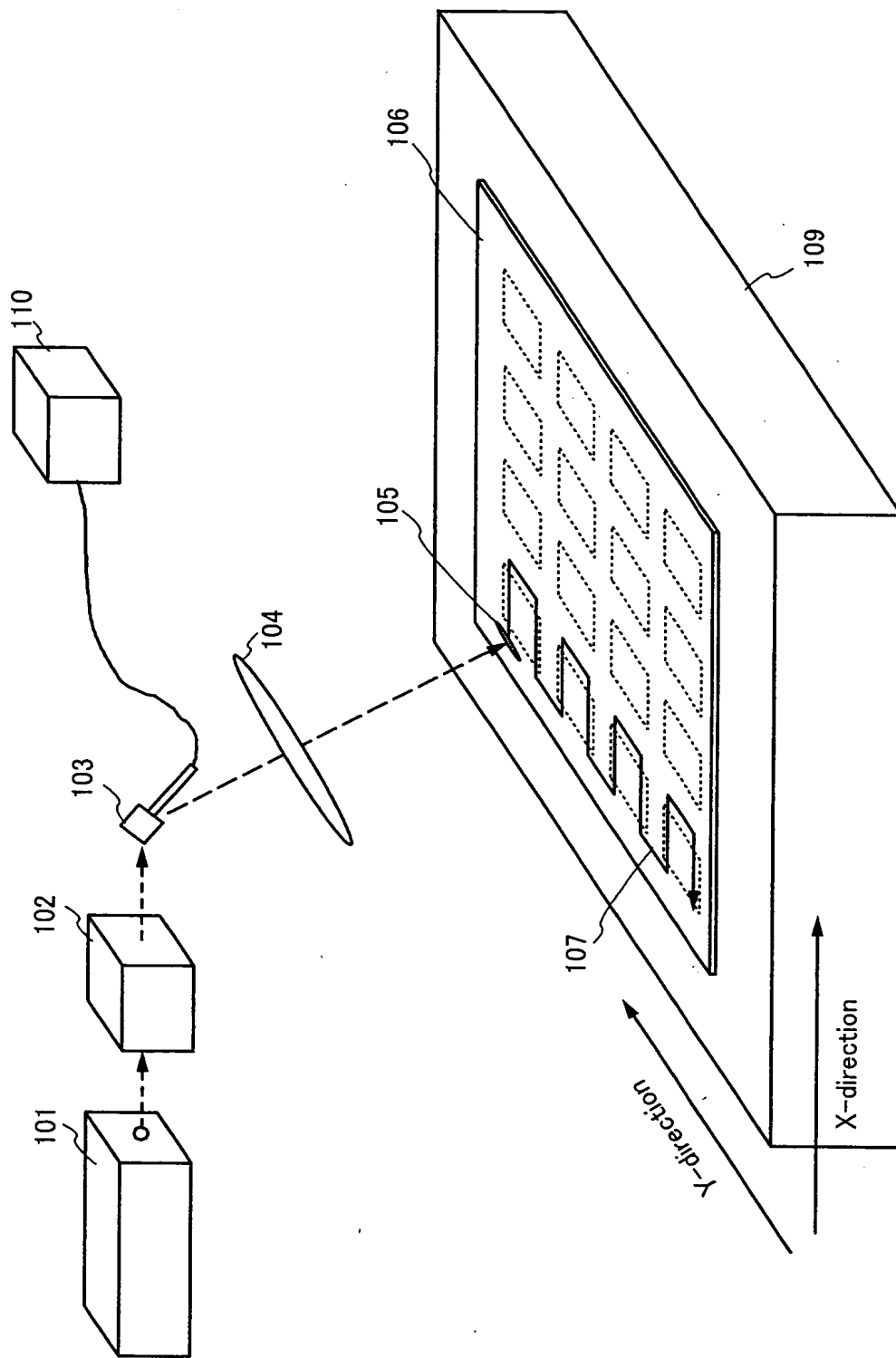


FIG. 3A

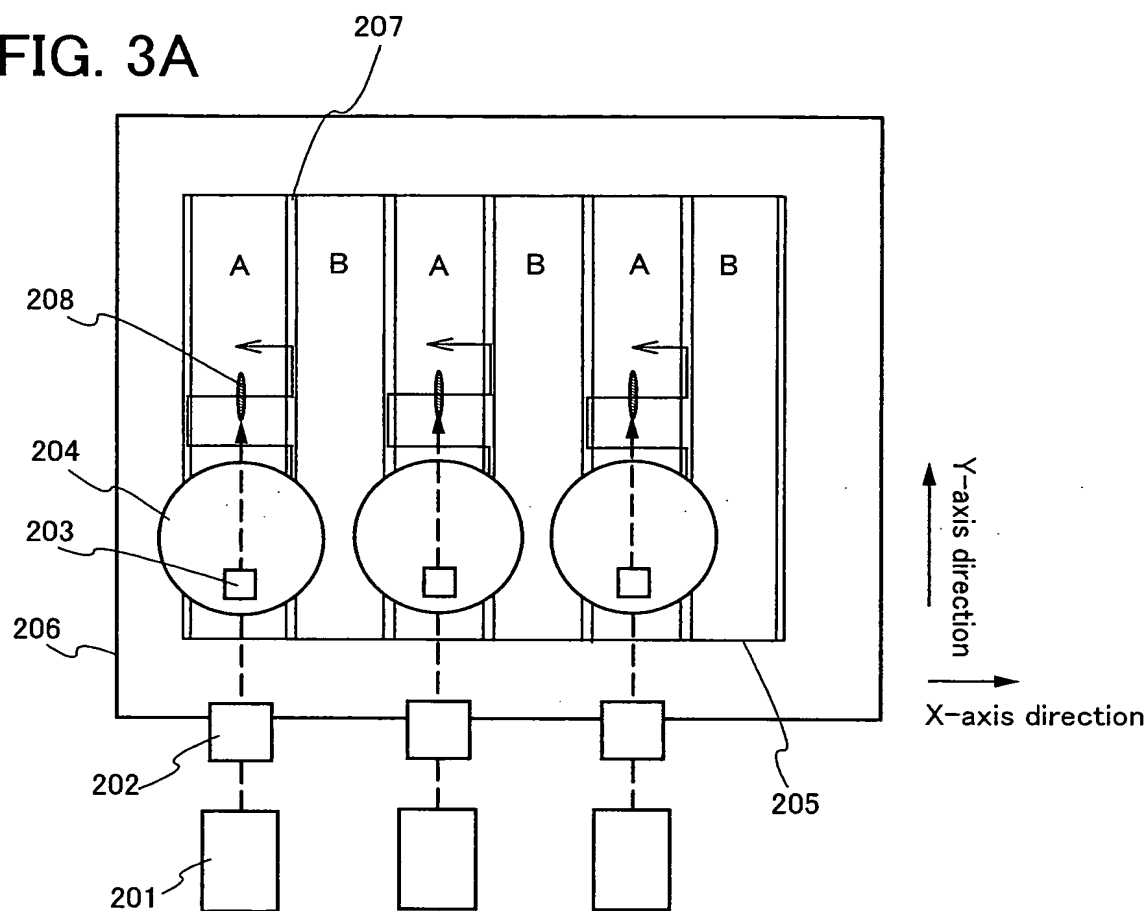
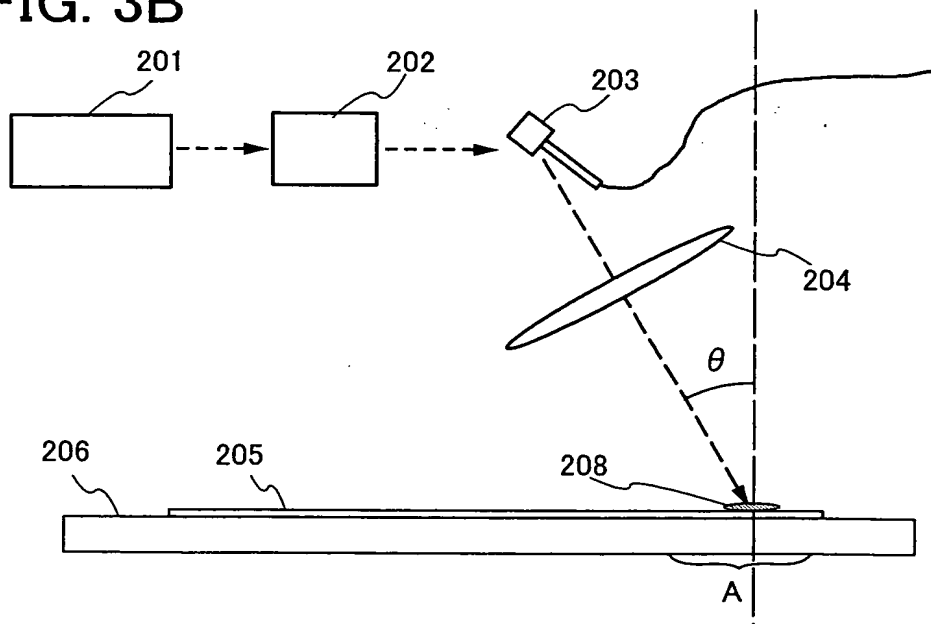


FIG. 3B



A detailed cross-sectional view of a TFT 422 device. The structure is built on a first substrate 400. At the base is a base insulating film 401. Above this is an interlayer insulating film 402. A first conductive film 403 is patterned into a gate electrode 416 and a channel-forming region 412. The channel-forming region 412 includes an impurity region 411. An insulator 404 is formed on top of the first conductive film 403. A second conductive film 406 is formed on top of the insulator 404. A protective film 407 is formed on top of the second conductive film 406. An organic compound layer 405 is formed on top of the protective film 407. A second substrate 409 is formed on top of the organic compound layer 405. An airspace 408 is formed between the second substrate 409 and the organic compound layer 405. A channel 417 is formed in the second conductive film 406. A second conductive film 406 is also formed on the first substrate 400. A channel 418 is formed in the second conductive film 406. A channel 419 is formed in the second conductive film 406. A channel 420 is formed in the second conductive film 406. A channel 421 is formed in the second conductive film 406. A channel 422 is formed in the second conductive film 406.

airspace 408	
protective film 407	
second conductive film 406	
organic compound layer 405	ETL(electron injecting layer) _ _ _ ETL(electron transporting layer) _ _ _ EML(light-emitting layer) _ _ _ HTL(hole transporting layer) _ _ _ HIL(hole injecting layer) _ _ _
first conductive film 403	
interlayer insulating film 402	

FIG. 5A

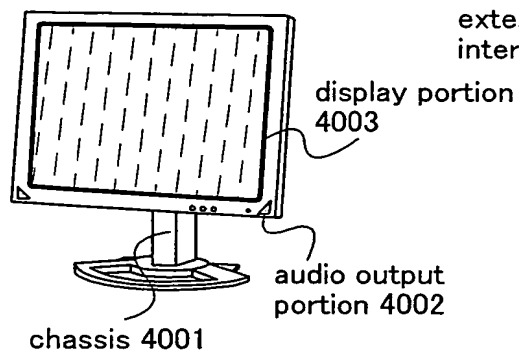


FIG. 5B

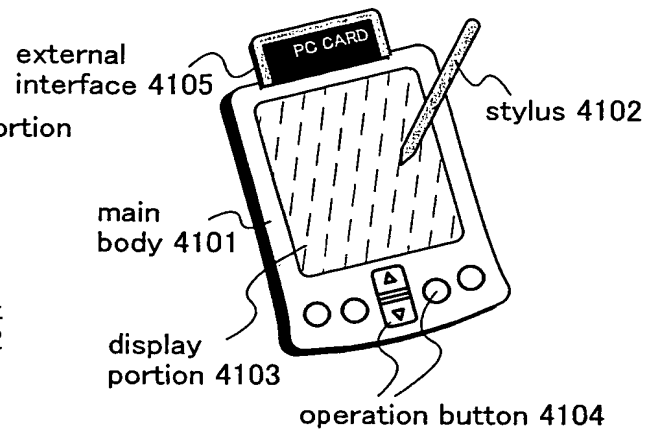


FIG. 5C

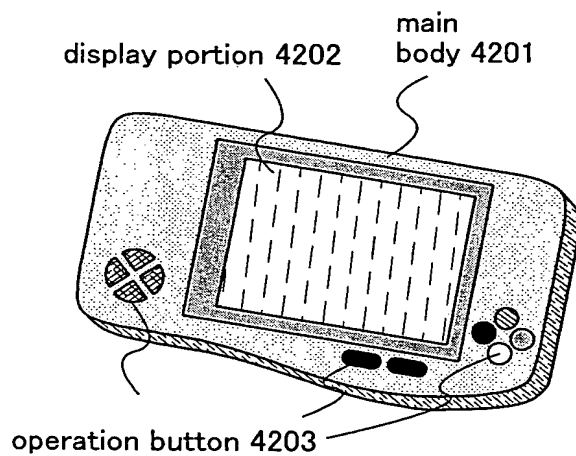


FIG. 5D

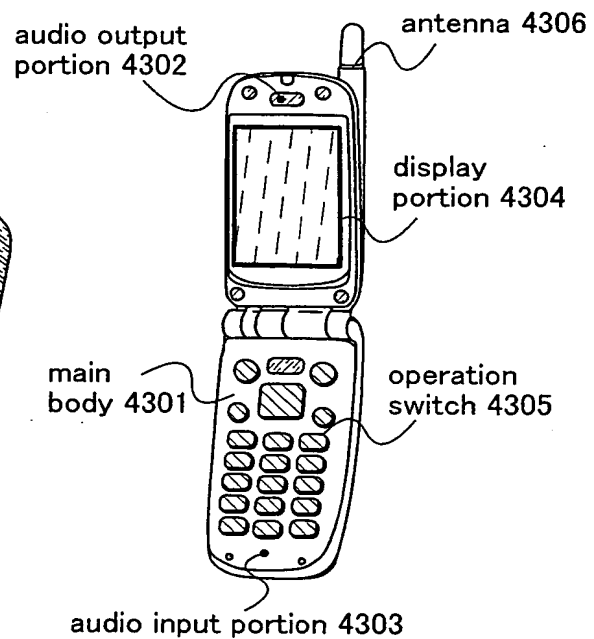


FIG. 5E

